# N-Channel 100-V (D-S) MOSFET

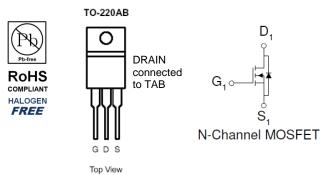
### **Key Features:**

- Low r<sub>DS(on)</sub> trench technology
- · Low thermal impedance
- · Fast switching speed

Typical .	Applica	ations:
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- · White LED boost converters
- Automotive Systems
- Industrial DC/DC Conversion Circuits

PRODUCT SUMMARY			
V <sub>DS</sub> (V)	$r_{DS(on)}(m\Omega)$	I⊳(A)	
100	78 @ V <sub>GS</sub> = 10V	51 <sup>a</sup>	
100	92 @ V <sub>GS</sub> = 5.5V	51	



ABSOLUTE MAXIMUM RATINGS ( $T_A = 25^{\circ}$ C UNLESS OTHERWISE NOTED)					
Parameter		Symbol	Limit	Units	
Orain-Source Voltage		$V_{DS}$	100	V	
Gate-Source Voltage		$V_{GS}$	±20	V	
Continuous Drain Current a	T <sub>A</sub> =25°C	I <sub>D</sub>	51	Α	
Ised Drain Current <sup>b</sup>		I <sub>DM</sub>	240	^	
Continuous Source Current (Diode Conduction) a		I <sub>S</sub>	90	Α	
Power Dissipation <sup>a</sup>	T <sub>A</sub> =25°C	$P_{D}$	300	W	
Operating Junction and Storage Temperature Range		$T_J,T_stg$	-55 to 175	°C	

THERMAL RESISTANCE RATINGS			
Parameter	Symbol	Maximum	Units
Maximum Junction-to-Ambient <sup>a</sup>	$R_{\theta JA}$	62.5	°C/W
Maximum Junction-to-Case	$R_{\theta JC}$	1	C/VV

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#### Notes

- a. Surface Mounted on 1" x 1" FR4 Board.
- b. Pulse width limited by maximum junction temperature

### **Electrical Characteristics**

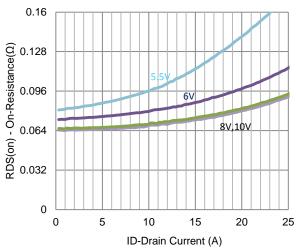
Parameter	Symbol	Test Conditions	Min	Тур	Max	Unit
Static						
Gate-Source Threshold Voltage	$V_{GS(th)}$	$V_{DS} = V_{GS}$ , $I_D = 250 \text{ uA}$	1			V
Gate-Body Leakage	I <sub>GSS</sub>	$V_{DS} = 0 \text{ V}, V_{GS} = \pm 20 \text{ V}$			±100	nA
Zero Gate Voltage Drain Current	lana	$V_{DS} = 80 \text{ V}, V_{GS} = 0 \text{ V}$			1	uA
Zero Gate Voltage Brain Current	I <sub>DSS</sub>	$V_{DS} = 80 \text{ V}, V_{GS} = 0 \text{ V}, T_{J} = 55^{\circ}\text{C}$			25	
On-State Drain Current	I <sub>D(on)</sub>	$V_{DS} = 5 \text{ V}, V_{GS} = 10 \text{ V}$	100			Α
Drain-Source On-Resistance	r	$V_{GS} = 10 \text{ V}, I_{D} = 20 \text{ A}$			78	mΩ
	r <sub>DS(on)</sub>	$V_{GS} = 5.5 \text{ V}, I_D = 18 \text{ A}$			92	
Forward Transconductance	g <sub>fs</sub>	$V_{DS} = 15 \text{ V}, I_{D} = 20 \text{ A}$		25		S
Diode Forward Voltage	$V_{SD}$	$I_{S} = 20 \text{ A}, V_{GS} = 0 \text{ V}$		0.93		V
		Dynamic				
Total Gate Charge	$Q_g$	$V_{DS} = 50 \text{ V}, V_{GS} = 5.5 \text{ V},$		13		nC
Gate-Source Charge	$Q_{gs}$	$V_{DS} = 30 \text{ V}, V_{GS} = 3.3 \text{ V},$ $I_{D} = 20 \text{ A}$		4.3		
Gate-Drain Charge	$Q_gd$	$I_D = 20 \text{ A}$		8.2		
Turn-On Delay Time	t <sub>d(on)</sub>	V -50 V B - 25 O		9		
Rise Time	t <sub>r</sub>	$V_{DS} = 50 \text{ V}, R_{L} = 2.5 \Omega,$ $I_{D} = 20 \text{ A},$ $V_{GEN} = 10 \text{ V}, R_{GEN} = 6 \Omega$		9		ns
Turn-Off Delay Time	$t_{d(off)}$			20		
Fall Time	t <sub>f</sub>			11		
Input Capacitance	C <sub>iss</sub>	V <sub>DS</sub> = 15 V, V <sub>GS</sub> = 0 V, f = 1 MHz		822		pF
Output Capacitance	C <sub>oss</sub>			83		
Reverse Transfer Capacitance	$C_{rss}$			72		

#### Notes

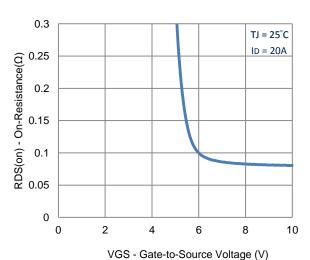
- a. Pulse test: PW <= 300us duty cycle <= 2%.
- b. Guaranteed by design, not subject to production testing.

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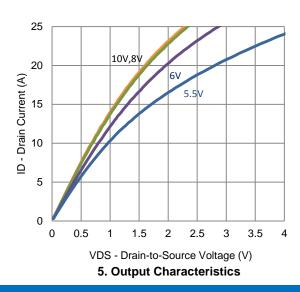
### **Typical Electrical Characteristics**



#### 1. On-Resistance vs. Drain Current



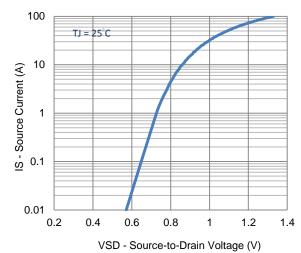
3. On-Resistance vs. Gate-to-Source Voltage



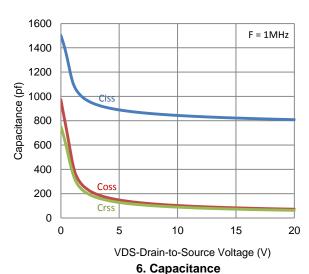
25
TJ = 25°C

20
(4)
tuesun 15
0
0
0
2
4
6
8
VGS - Gate-to-Source Voltage (V)

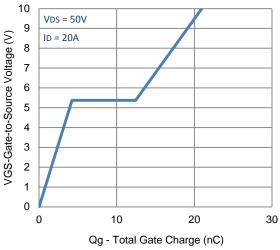
2. Transfer Characteristics



4. Drain-to-Source Forward Voltage

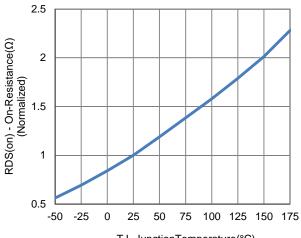


### **Typical Electrical Characteristics**

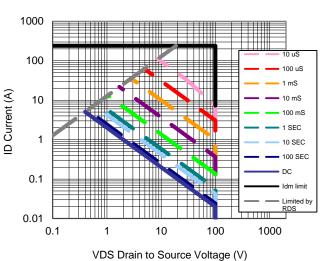


2g - Total Gate Charge (nC)

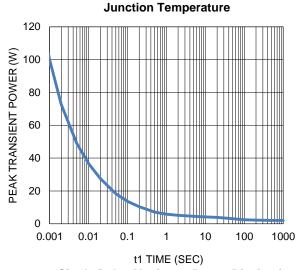
7. Gate Charge



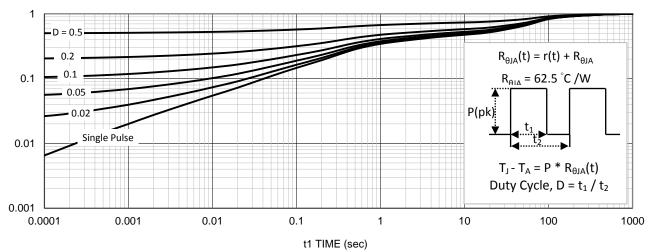
TJ -JunctionTemperature(°C)
8. Normalized On-Resistance Vs



9. Safe Operating Area



10. Single Pulse Maximum Power Dissipation



11. Normalized Thermal Transient Junction to Ambient

## **Package Information**

